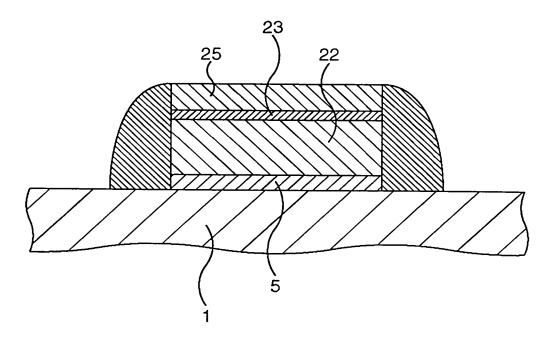
FIG. 1



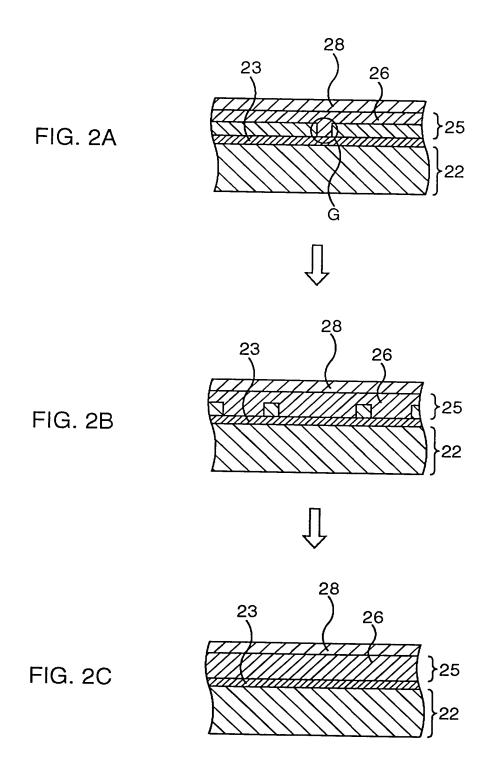
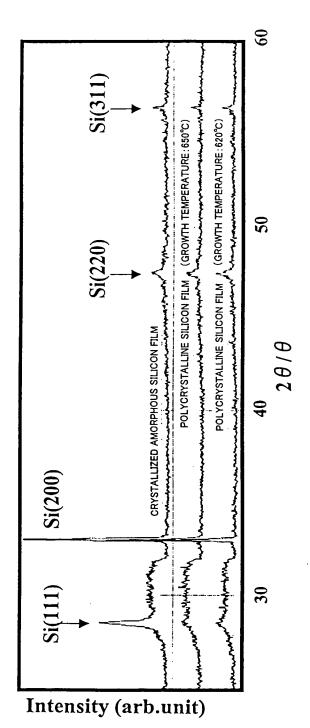


FIG. 3A



<X-RAY DIFFRACTION RESULTS OF VARIOUS SILICON FILMS>

FIG. 3B

BAS	BASE SILICON FILM	SILICIDE RESISTANCE VALUE
POLYCRY	POLYCRYSTALLINE SILICON FILM	7. 2 (Ω/sq)
AMORPHOUS	WITHOUT CRYSTALLIZATION	6. 4 (Q/sq)
SILICON FILM	WITH CRYSTALLIZATION	5. 7 (Q/sq)

<RESISTANCES OF CoSi2 FOMED ON VARIOUS SILICON FILMS>

FIG. 4

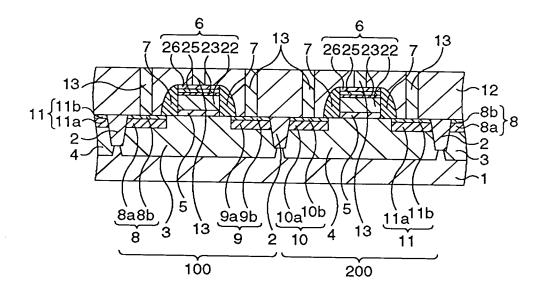


FIG. 5A

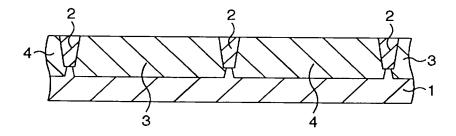


FIG. 5B

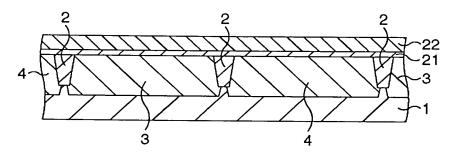


FIG. 5C

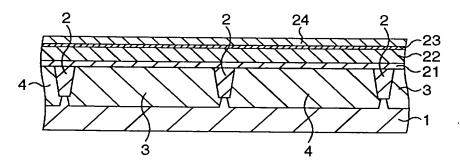
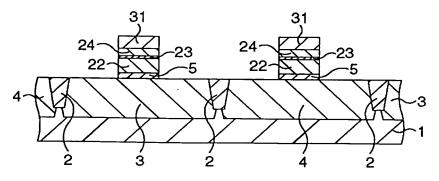
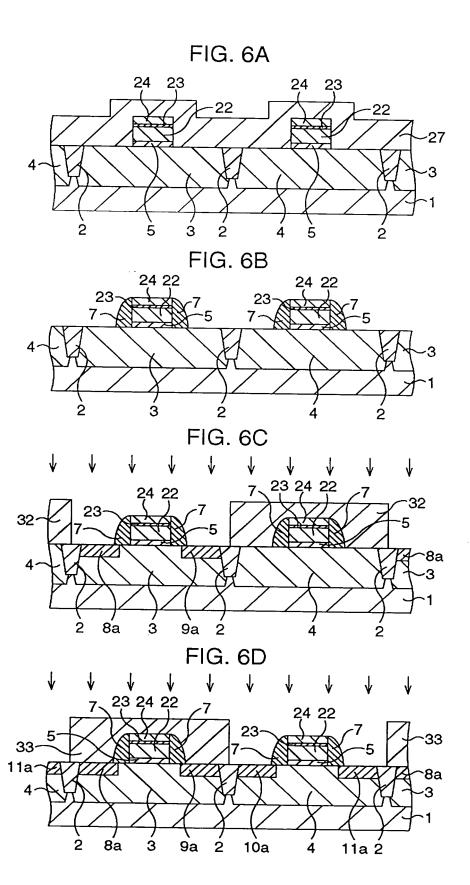


FIG. 5D





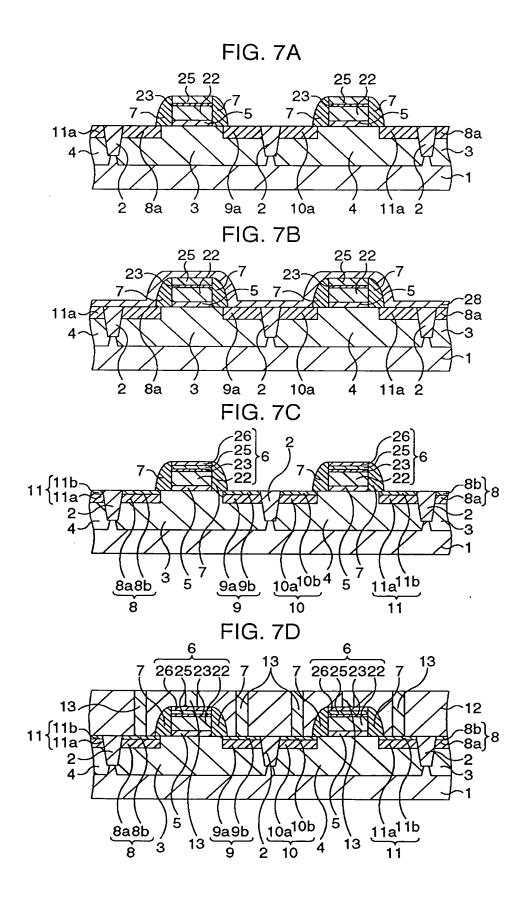


FIG. 8A

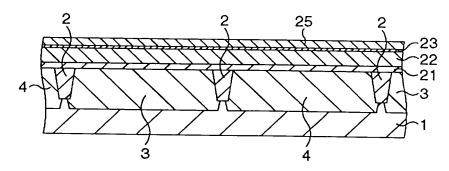


FIG. 8B

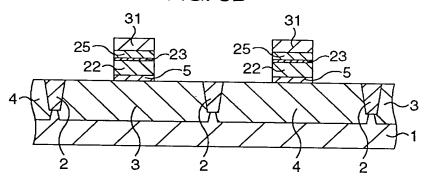


FIG. 8C

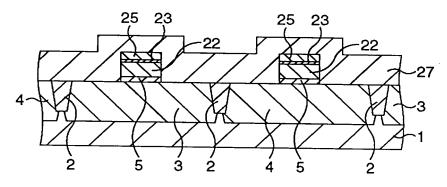


FIG. 8D

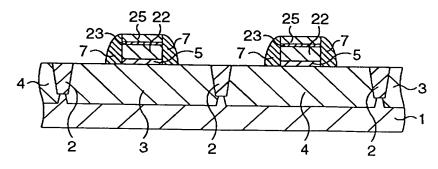


FIG. 9A

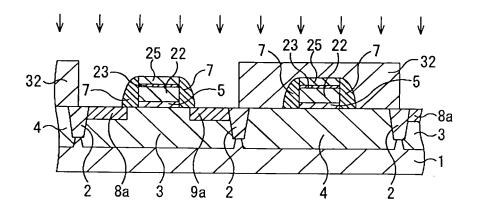


FIG. 9B

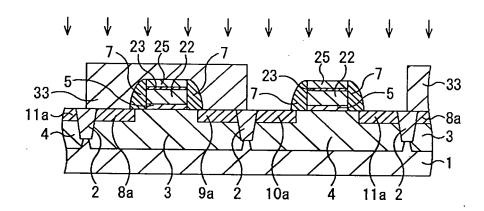
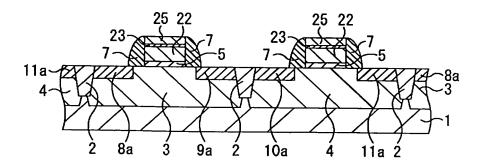
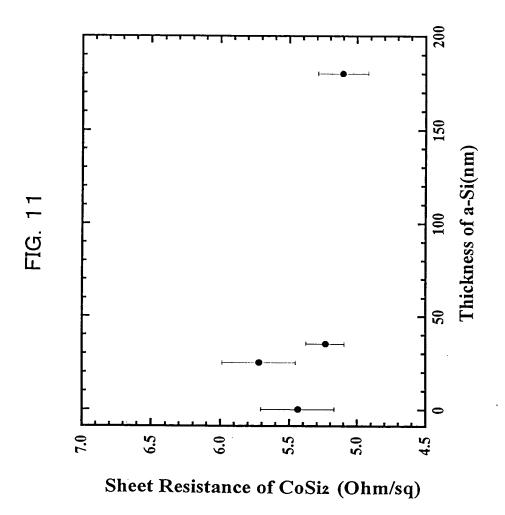


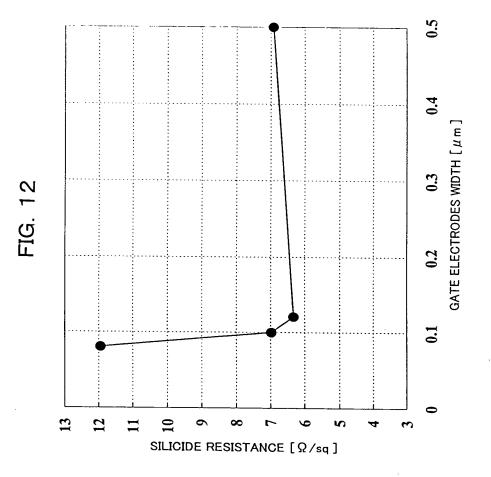
FIG. 9C



CASE OF TWO-LAYER POLYCRYSTALLINE SILICON FILMS (a-Si THICKNESS: 35nm) CASE OF TWO-LAYER POLYCRYSTALLINE SILICON FILMS (a-Si THICKNESS: 25nm) CASE OF SINGLE-LAYER POLYCRYSTALLINE FORMATION DEFECT SILICON FILM NSD-P+ PSD-B+

FIG. 1(





**<OVER SILICIDIZATION REACTION POINT EXAMINED IN** FIG. 14 CoSiz <PHOTOGRAPH OF CROSS SECTION OF CoSi2 FORMATION DEFECT POINT>

PHOTOGRAPH OF CROSS SECTION>